

TO-92 Plastic-Encapsulate Transistors

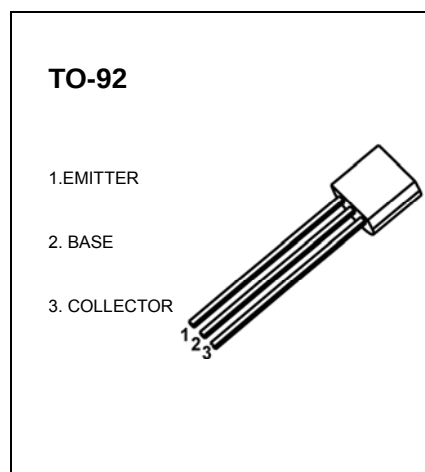
M8550 TRANSISTOR (PNP)

FEATURES

- Power Dissipation

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-800	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	125	°C
T_{stg}	Storage Temperature	-55-125	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}^*$	$I_C = -0.1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E = -100\mu A, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -5mA$	45		
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -100mA$	80	400	
	$h_{FE(3)}$	$V_{CE} = -1V, I_C = -800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$ $f = 30MHz$	150		MHz

*Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.